

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A method of modulating an optical signal comprises the steps of:

providing a waveguide defining a light path for said optical signal;
providing a resonant cavity in said light path in said waveguide; and
altering the transmission characteristic of the resonant cavity by application of an electric field whereby to control the degree of transmission of light of a selected frequency propagating in said light path.

2. (original) The modulation method of claim 1, wherein the waveguide-providing step comprises providing a waveguide selected in the group consisting of photonic crystal waveguides, total internal reflection waveguides, and waveguides combining the principles of photonic crystal waveguides and total internal reflection waveguides.

3. (original) The modulation method of claim 1, wherein the resonant-cavity-providing step comprises providing a plurality of holes defining a photonic bandgap device in the waveguide.

4. (original) The modulation method of claim 1, wherein the waveguide-providing step comprises providing a waveguide having a silicon (Si) core layer clad with silica (SiO₂).

5. (original) The modulation method of claim 4, wherein the transmission-characteristic-altering step comprises the step of applying an electric field to the resonant cavity whereby to cause the MOS effect and alter the Q-factor of the cavity.

6. (original) The modulation method of claim 1, further comprising the step of providing a p-n junction in the waveguide at the resonant cavity, wherein the

transmission-characteristic-altering step comprises the step of applying a biasing electric field to the p-n junction whereby to alter the Q-factor of the cavity.

7. (currently amended) An optical signal modulator, comprising:
a waveguide defining a light path for an optical signal;
a resonant cavity in said light path in said waveguide; and
a control unit for altering the transmission characteristic of the resonant cavity by application of an electric field whereby to control the degree of transmission of light of a selected frequency propagating in said light path.
8. (original) The optical signal modulator of claim 7, wherein the waveguide is selected in the group consisting of photonic crystal waveguides, total internal reflection waveguides, and waveguides combining the principles of photonic crystal waveguides and total internal reflection waveguides.
9. (original) The optical signal modulator of claim 7, wherein the resonant cavity comprises a plurality of holes defining a photonic bandgap device in the waveguide.
10. (original) The optical signal modulator of claim 7, wherein the waveguide has a silicon (Si) core layer clad with silica (SiO₂).
11. (original) The optical signal modulator of claim 10, wherein the control unit is adapted, in use, to apply an electric field to the resonant cavity whereby to cause the MOS effect and alter the Q-factor of the cavity.
12. (original) The optical signal modulator of claim 7, and comprising a p-n junction provided in the waveguide at the resonant cavity, wherein the control means is adapted, in use, to apply a biasing electric field to the p-n junction whereby to alter the Q-factor of the cavity.
13. (withdrawn) A planar silicon waveguide defining a light path, the waveguide having a resonant cavity formed in the light path.

Appl. No.: 10/664,517
Amdt. Dated: November 30, 2005
Reply to Office Action of: September 14, 2005

14. (withdrawn) The planar silicon waveguide of claim 13, wherein the resonant cavity is constituted by a photonic bandgap device.